

LDP2013DT1G

20V P-Channel Enhancement-Mode MOSFET

1. FEATURES

- $V_{DS} = -20V$
- $R_{DS(ON)}, V_{GS@-4.5V}, I_{DS@-2A} \leq 100m\Omega$
- $R_{DS(ON)}, V_{GS@-2.5V}, I_{DS@-1.8A} \leq 130m\Omega$
- We declare that the material of product compliance with RoHS requirements and Halogen Free.

2. APPLICATIONS

- Simple drive requirement
- Small package outline
- Surface mount device

3. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LDP2013DT1G	DP3	4000/Tape&Reel

4. MAXIMUM RATINGS($T_a = 25^\circ C$)

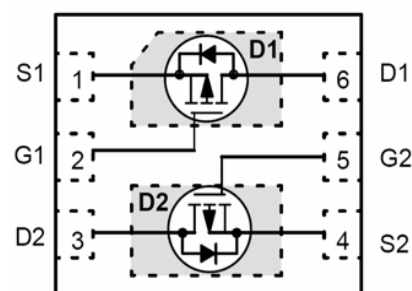
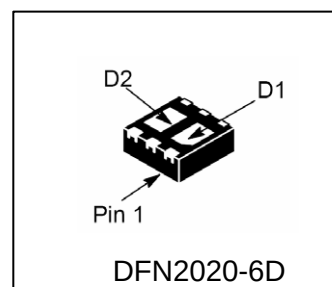
Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-to-Source Voltage – Continuous	V_{GS}	± 12	V
Drain Current			
– Continuous $T_A = 25^\circ C$	I_D	-3	A
– Pulsed (Note 1)	I_{DM}	-12	

5. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Power Dissipation	PD	1.4	W
Thermal Resistance, Junction-to-Ambient(Note 2)	$R_{\theta JA}$	85	$^\circ C/W$
Junction and Storage temperature	T_J, T_{stg}	$-55 \sim +150$	$^\circ C$

1.Repetitive Rating: Pulse width limited by the maximum junction temperature.

2.1-in² 2oz Cu PCB board.

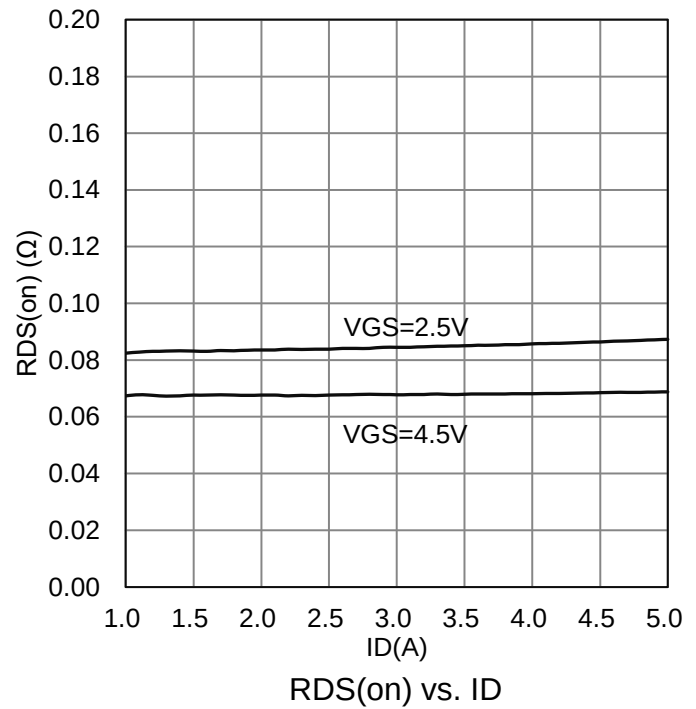
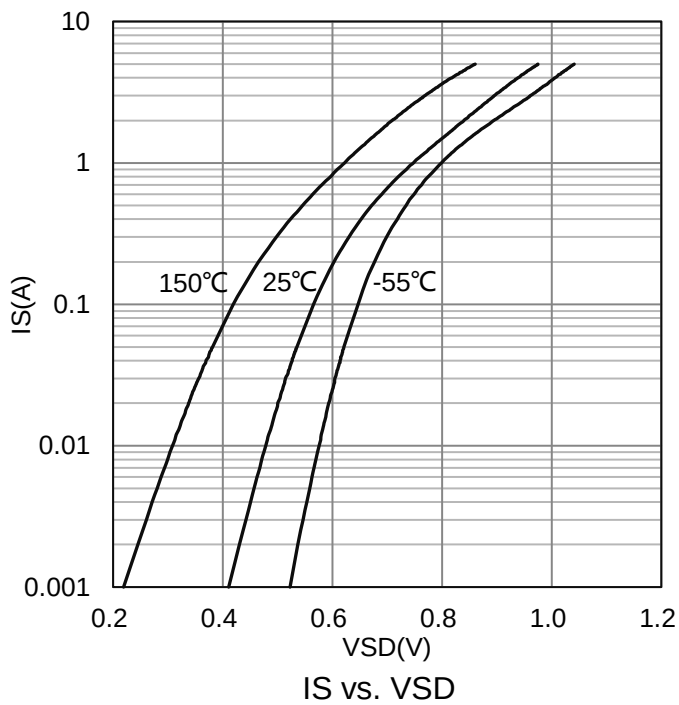
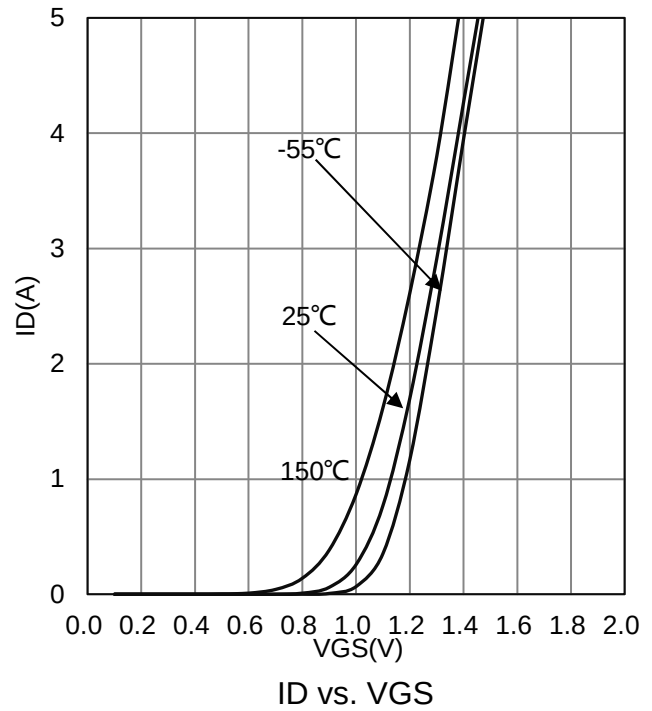
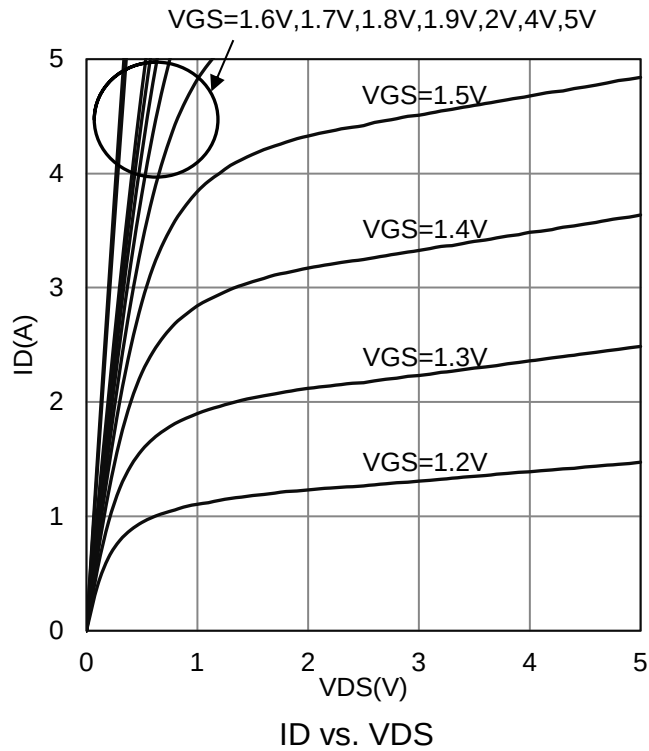


6. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

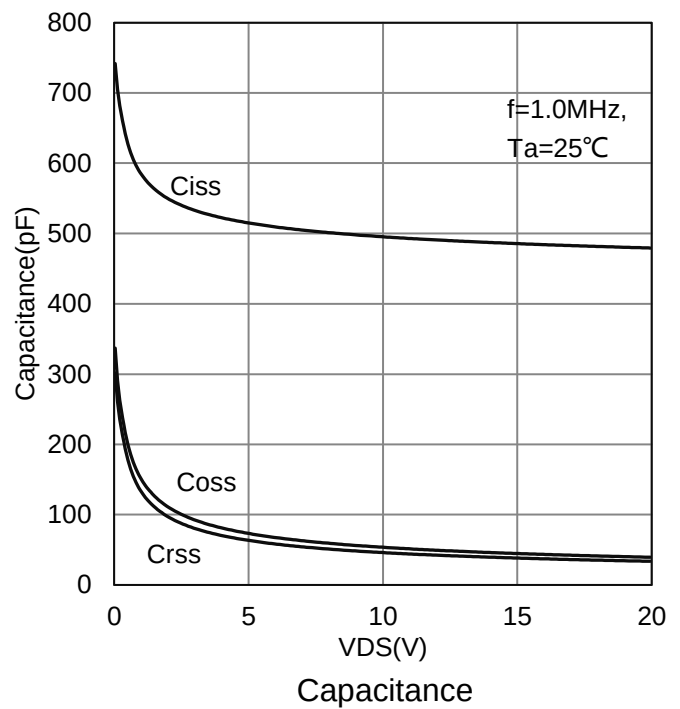
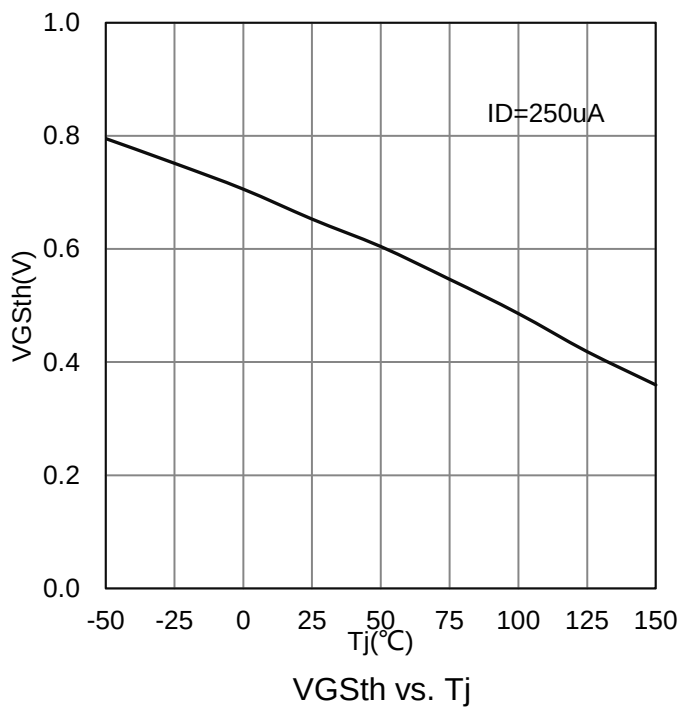
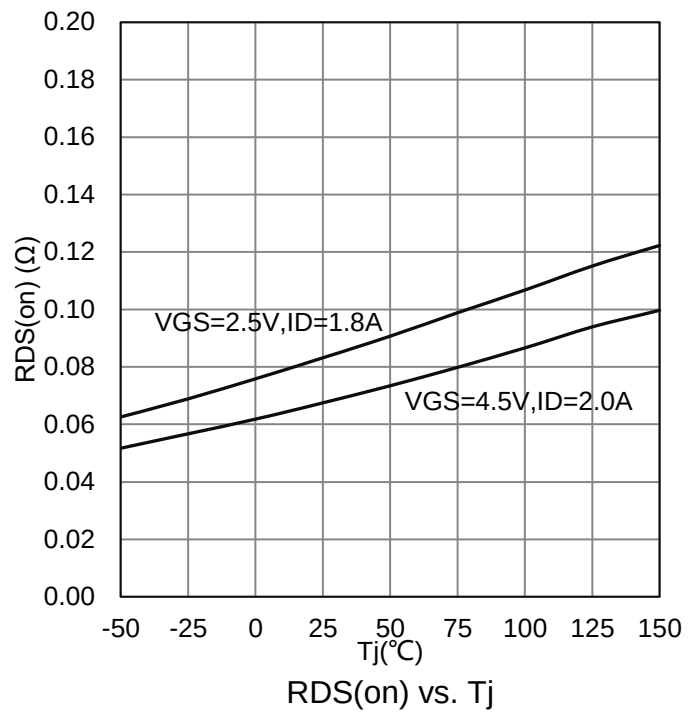
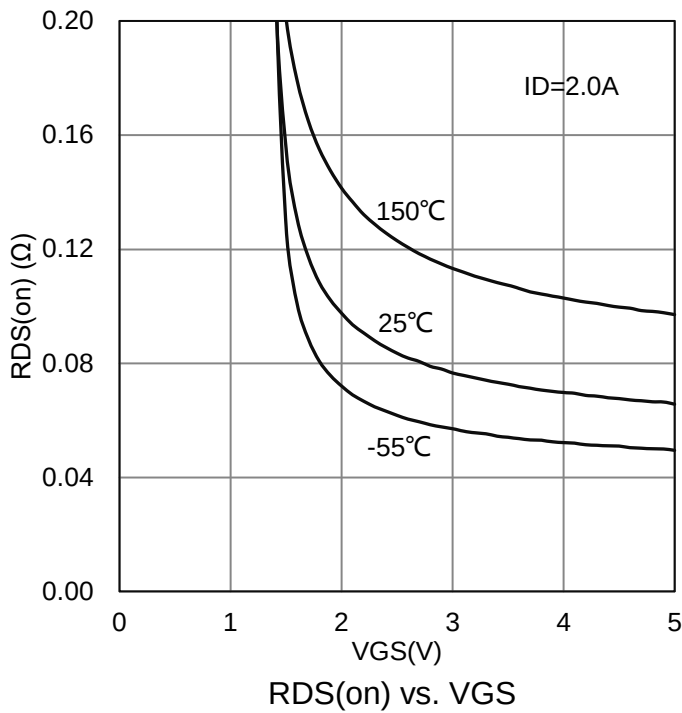
Characteristic		Symbol	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage (VGS = 0 V, ID = -250 μ A)		VBRDSS	-20	-	-	V
Gate-Source Threshold Voltage (VDS = VGS, ID = -250 μ A)		VGS(th)	-0.4	-	-0.9	V
Gate-Body Leakage Current (VDS = 0 V, VGS = $\pm$ 12 V)		IGSS	-	-	$\pm$ 100	nA
Zero Gate Voltage Drain Current (VDS = -16 V, VGS = 0 V)		IDSS	-	-	-1	μ A
Drain-Source On-Resistance(Note 3) (VGS = -4.5 V, ID = -2 A) (VGS = -2.5 V, ID = -1.8 A)		RDS(ON)	- -	- -	100 130	m Ω
Diode Forward Voltage (IS = -1 A, VGS = 0 V)		VSD	-0.4	-0.8	-1.2	V
Dynamic						
Total Gate Charge	(VDS = -10 V, VGS = -4.5 V, ID = -2 A)	Qg	-	5.4	-	nC
Gate to Source Charge		Qgs	-	0.6	-	
Gate to Drain Charge		Qgd	-	1.6	-	
Turn-on Delay Time	(VDS = -10 V, ID = -1 A, RL = 10 Ω , VGS = -4.5 V, RG = 6.2 Ω)	td(on)	-	4.5	-	nS
Rise Time		tr	-	6.2	-	
Turn-Off Delay Time		td(off)	-	95	-	
Fall Time		tf	-	47	-	
Input Capacitance	(VDS = -10 V, VGS = 0 V, f = 1MHz)	Ciss	-	497	-	pF
Output Capacitance		Coss	-	55	-	
Reverse Transfer Capacitance		Crss	-	47	-	

3. Pulse test: PW $\leq$ 300 μ s duty cycle $\leq$ 2%.

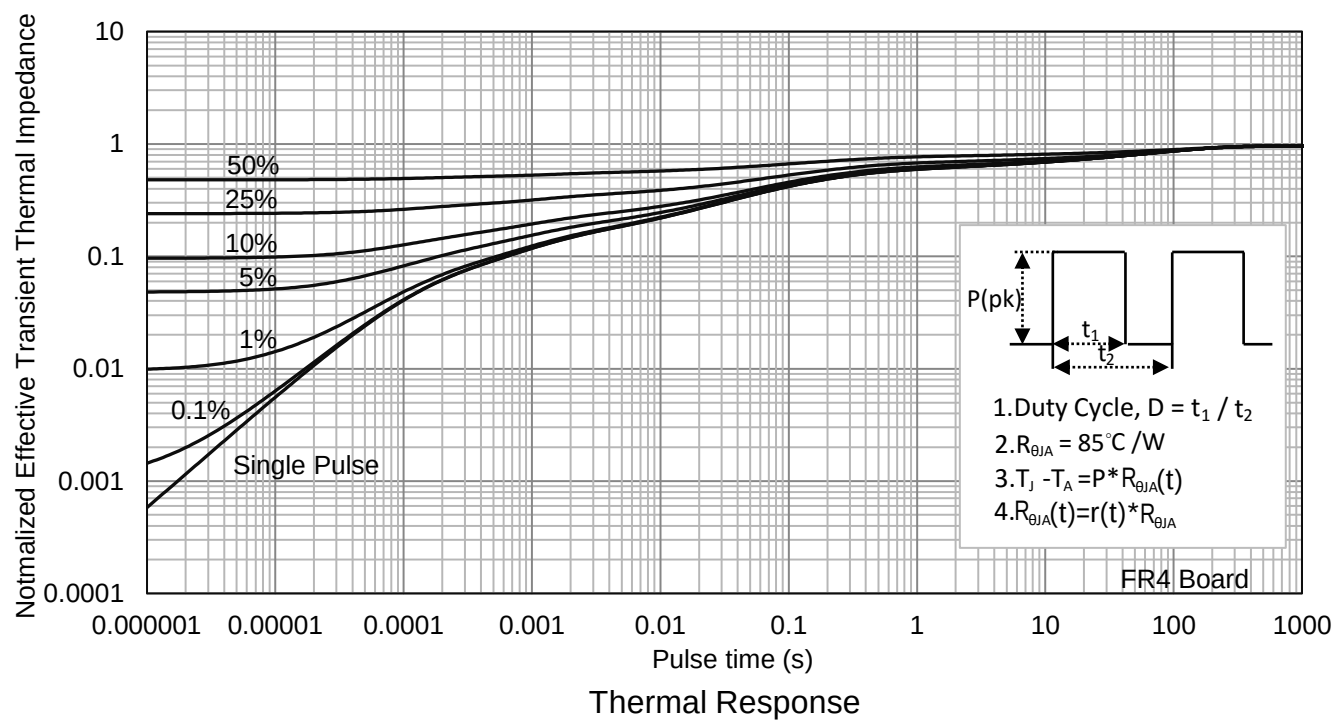
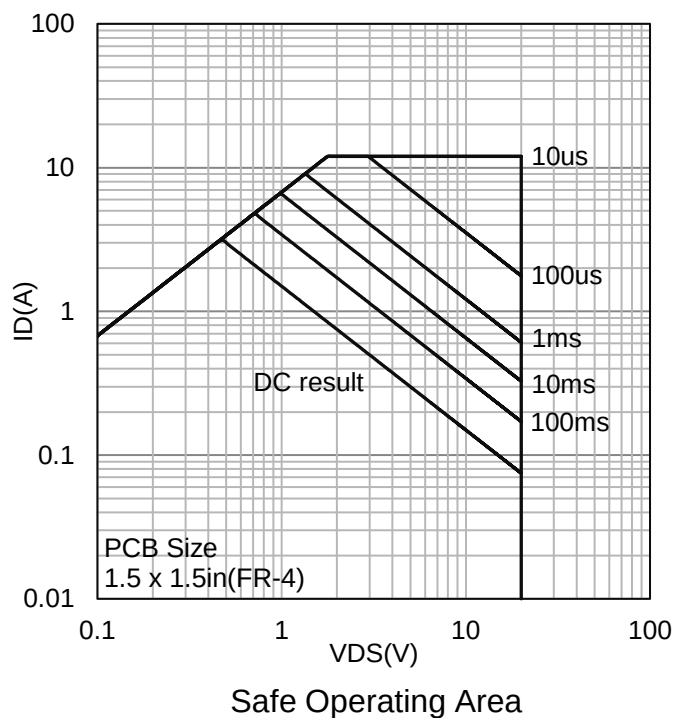
7. ELECTRICAL CHARACTERISTICS CURVES



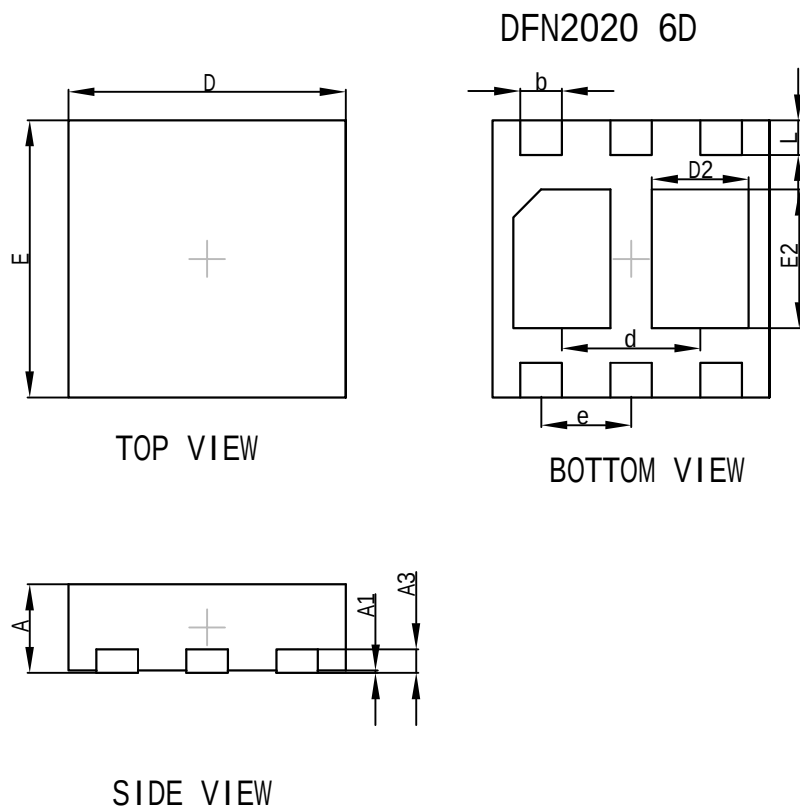
7. ELECTRICAL CHARACTERISTICS CURVES(Con.)



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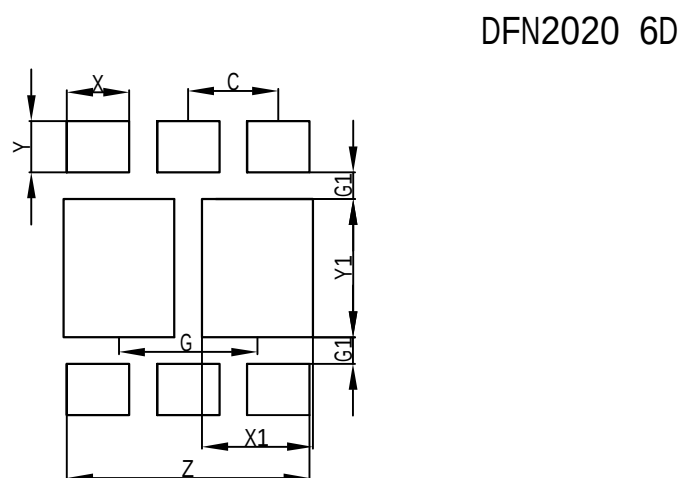


8.OUTLINE AND DIMENSIONS (Unit:mm)



DFN2020 6D			
Dim	Min	Typ	Max
D	1.95	2.00	2.05
E	1.95	2.00	2.05
e	-	0.65	-
L	0.20	0.25	0.30
b	0.25	0.30	0.35
d	-	1.00	-
A	0.60	0.65	0.70
A1	0	0.02	0.05
A3	-	0.152	-
E2	0.95	1.00	1.05
D2	0.65	0.70	0.75
All Dimensions in mm			

9.SOLDERING FOOTPRINT



Dimensions	(mm)
X	0.45
Y	0.37
X1	0.80
Y1	1.00
C	0.65
G	1.00
G1	0.19
Z	1.75

DISCLAIMER

- Curve guarantee in the specification. The curve of test items with electric parameter is used as quality guarantee. The curve of test items without electric parameter is used as reference only.
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